

# 2SK1517, 2SK1518

# Silicon N Channel MOS FET

REJ03G0947-0200

(Previous: ADE-208-1287)

Rev.2.00 Sep 07, 2005

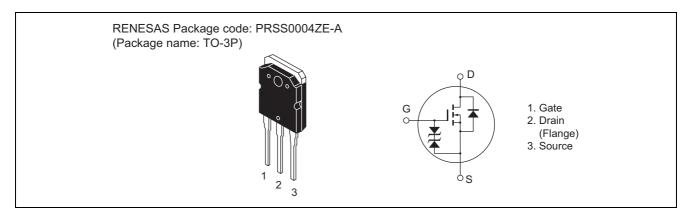
### **Application**

High speed power switching

#### **Features**

- Low on-resistance
- High speed switching
- Low drive current
- Built-in fast recovery diode ( $t_{rr} = 120 \text{ ns}$ )
- Suitable for motor control, switching regulator, DC-DC converter

#### **Outline**



# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK1517	V <sub>DSS</sub>	450	V
	2SK1518		500	
Gate to source voltage		$V_{GSS}$	±30	V
Drain current		I <sub>D</sub>	20	Α
Drain peak current		I <sub>D(pulse)</sub> *1	80	Α
Body to drain diode reverse drain current		I <sub>DR</sub>	20	Α
Channel dissipation		Pch <sub>*2</sub>	120	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	−55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value at  $T_C = 25$ °C

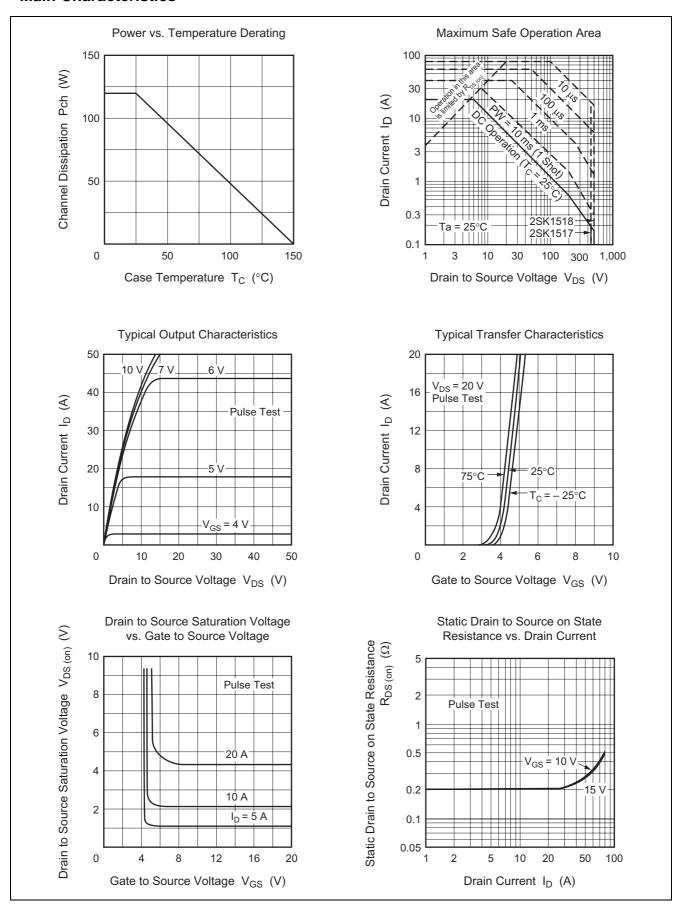
#### **Electrical Characteristics**

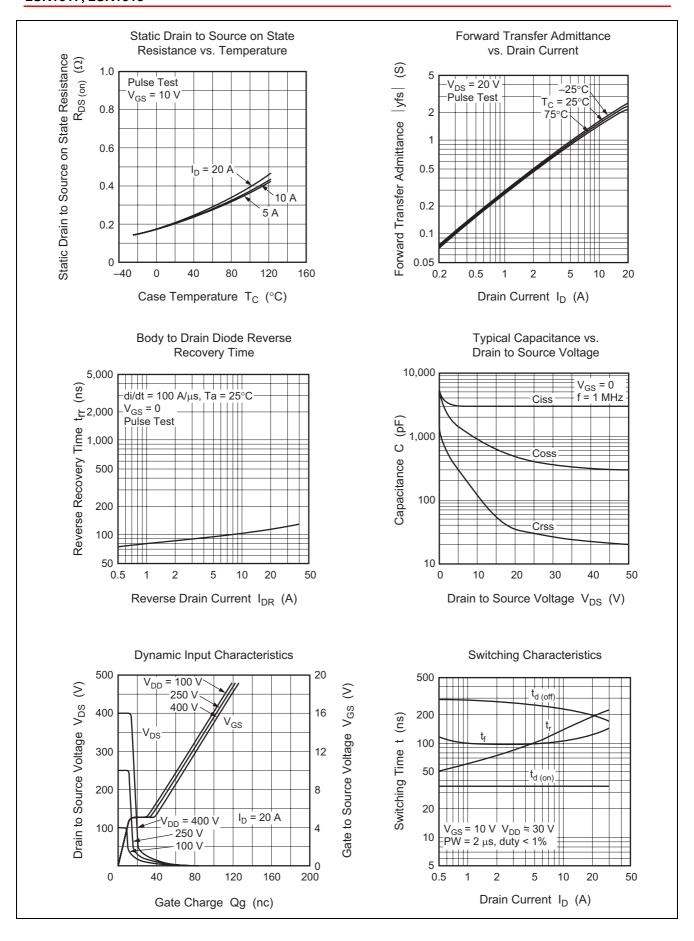
 $(Ta = 25^{\circ}C)$ 

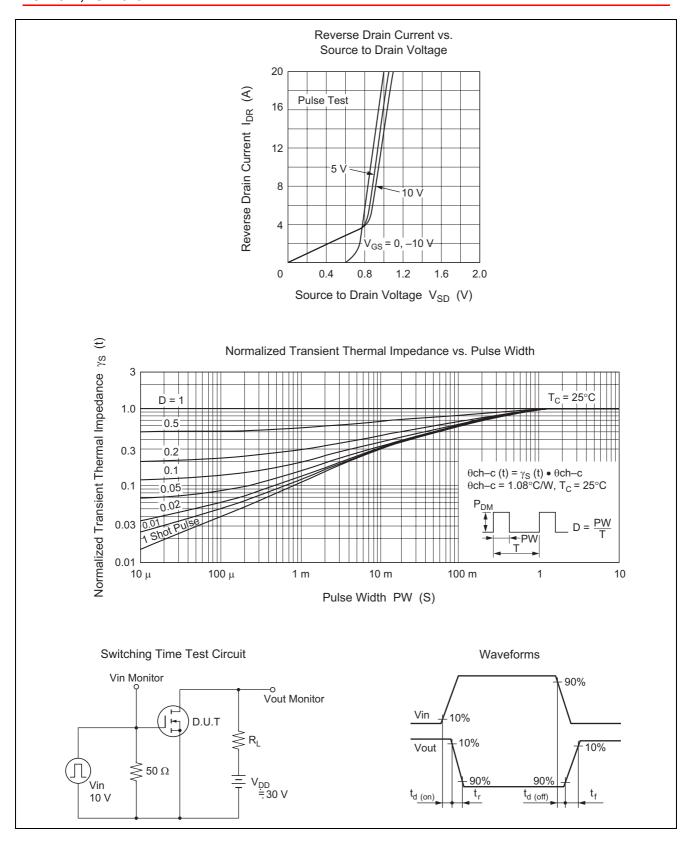
Item		Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source	2SK1517	$V_{(BR)DSS}$	450	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
breakdown voltage	2SK1518		500				
Gate to source breakdowr	n voltage	$V_{(BR)GSS}$	±30	1		V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current		I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain	2SK1517	I <sub>DSS</sub>	_	_	250	μΑ	$V_{DS} = 360 \text{ V}, V_{GS} = 0$
current	2SK1518						$V_{DS} = 400 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage		$V_{GS(off)}$	2.0	1	3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on	2SK1517	R <sub>DS(on)</sub>	_	0.20	0.25	Ω	$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V}^{*3}$
state resistance	2SK1518		_	0.22	0.27		
Forward transfer admittance		y <sub>fs</sub>	10	16	_	S	$I_D = 10 \text{ A}, V_{DS} = 10 \text{ V}^{*3}$
Input capacitance		Ciss	_	3050	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance		Coss	_	940	_	pF	f = 1 MHz
Reverse transfer capacitance		Crss	_	140	_	pF	
Turn-on delay time		t <sub>d(on)</sub>	_	35	_	ns	$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time		t <sub>r</sub>	_	130	_	ns	$R_L = 3 \Omega$
Turn-off delay time		$t_{d(off)}$	_	240	_	ns	
Fall time		t <sub>f</sub>	_	105	_	ns	
Body to drain diode forward voltage		$V_{DF}$	_	1.0	_	V	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0
Body to drain diode reverse recovery		t <sub>rr</sub>	_	120	_	ns	$I_F = 20 \text{ A}, V_{GS} = 0,$
time							$di_F/dt = 100 A/\mu s$

Note: 3. Pulse test

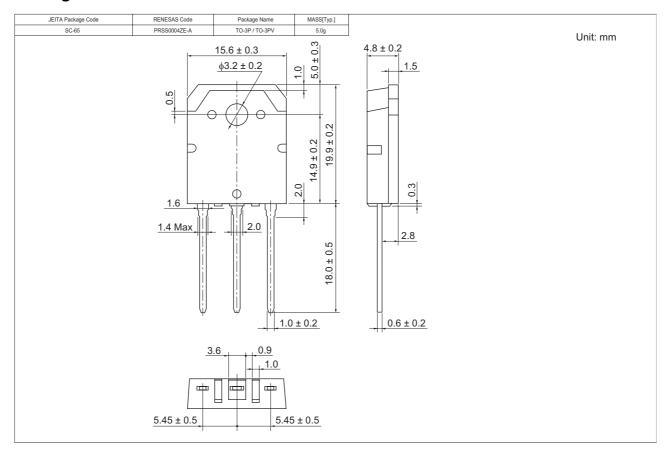
#### **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

Part Name	Quantity	Shipping Container
2SK1517-E	360 pcs	Box (Tube)
2SK1518-E	360 pcs	Box (Tube)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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